

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	5	((("20020102821") or ("20030001157") or ("6456013") or ("6194254") or ("20030067458") or ("EP1298634"))).PN.	US-PGPUB; USPAT	OR	OFF	2006/12/30 21:53
S7	11	"1298634"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 16:00
S8	1	("20040218109").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/21 16:35
S14	5	((("6456013") or ("20030001157") or ("20020102821") or ("6194154") or ("20030067458"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/02 14:05
S17	24818	((thin adj film) TFT) and ((semiconductor adj channel\$5) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:04
S18	4238	S17 and (laser and irradiat\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:13
S20	96464	((thin adj film adj transistor\$5) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:25
S21	0	((laser adj beam\$5) and irradiat\$5) same ((semiconductor adj channel\$5) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:26
S22	1795	(laser adj beam\$5) same ((semiconductor adj channel\$5) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:38

EAST Search History

S23	532	S20 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:28
S25	87	S23 and ("349"/\$.ccls. 257/59,72. ccls. 345/92.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:12
S26	299	((thin adj film adj transistor\$5) TFT) and (semiconductor adj channel\$5) and (semiconductor adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:37
S27	3123	(laser adj beam\$5) same (semiconductor adj (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:38
S28	14	S26 and S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 15:24
S29	1	("6495405").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/02 15:24
S30	3	("5821562" "6177301" "6211536").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/02 15:25
S31	75	(semiconductor adj channel\$5) and stripe\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:23
S39	8065	S17 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:54

EAST Search History

S40	316	S39 and 349/42-43.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:57
S41	701	S39 and 257/59,72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:55
S42	73	S39 and 345/92.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:56
S43	608	S41 not S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:56
S44	693	S41 not S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:56
S45	1035	S39 and (349/42-43.ccls. 257/59,72. ccls. 345/92)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:06
S46	719	S45 not S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:57
S47	77804	((thin adj film) TFT) and ((channel channels) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:05

EAST Search History

S48	35292	((thin adj film) TFT) same ((channel channels) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 17:20
S49	9617	S48 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:06
S50	1420	S49 and (349/42-43.ccls. 257/59,72. ccls. 345/92)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/15 03:02
S51	17925	((channel channels) (semiconductor adj layer)) same (stripe stripes (straight adj (line lines)) (zig-zag adj (line lines)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:16
S52	1601	S51 and ((thin adj film) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 17:24
S54	287	S52 and ("349"/\$.ccls. 257/59,72. ccls. 345/92)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 17:27
S55	2	((("5534716") or ("5808321")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/03 19:14
S56	3	((("5808321") or ("5534716") or ("6853002")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/03 19:14
S57	82770	((thin adj film) TFT) and ((channel channels) (semiconductor adj (film layer)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:11

EAST Search History

S58	24045	S57 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:17
S59	454	S58 and 349/42-43.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:59
S60	442	S59 not S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:59
S61	136	S58 and 345/92.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 20:13
S62	135	S61 not S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:59
S63	1018	S58 and 257/59,72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 20:13
S64	957	S63 not S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:51
S65	96750	((thin near film near transistor) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:52

EAST Search History

S66	24774	S65 and channel\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:53
S67	5777	S66 and ((peripheral near circuit) (driving near circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:53
S68	5342	S67 and (crystal\$8)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:54
S69	881	S68 and (257/59,72,66,74.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 16:05
S70	1	("20040218109").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 15:11
S71	5	((("20020102821") or ("20030001157") or ("6456013") or ("6194254") or ("20030067458"))). PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:20
S72	19	("4466179" "4528480" "5589406" "5616506" "5712191" "5789763" "5808318" "5808595" "5824574" "5942856" "5943593" "5953597" "5981974" "6028577" "6037924" "6057183" "6096581" "6160272" "6252248").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/04 16:14
S73	0	("2003001157").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:20
S74	1	("20030001157").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:21
S75	1	("20020102821").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:21
S76	1	("6194254").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:26

EAST Search History

S77	1945	driving adj ((thin adj film adj transistor) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 19:27
S78	1109	S77 and channel\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 19:32
S79	1	("6303963").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:32
S80	3	((("20030231149") or ("20050092997") or ("20050095760")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 11:59
S81	363	display and laser and semiconductor adj energy adj laboratory and photograph	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:04
S82	6981	drive and zig-zag	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:01
S83	1190	S82 and display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:01
S84	501	S83 and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:02
S85	188	S84 and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:03

EAST Search History

S86	139	staggered adj channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:03
S88	18	S86 and semiconductor	US-PGPUB; USPAT	OR	ON	2005/05/05 12:09
S89	6057	semiconductor and ((thin adj film adj transistor) TFT) and channel\$1 and laser	US-PGPUB; USPAT	OR	ON	2005/05/05 12:11
S90	7340	((thin adj film adj transistor) TFT) and channel\$1 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:11
S91	3463	S90 and display and drive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:12
S93	2286	S91 and stag\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:15
S94	2224	S93 and crystal\$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:19
S95	21309	(process method) same (thin adj film adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:20
S96	6289	S95 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:20

EAST Search History

S97	5102	S96 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:20
S98	2163	S97 and "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:22
S99	1905	S98 and display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:22
S10 1	1879	S99 and crystal\$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:25
S10 2	1695	S101 and view	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:26
S10 3	159	S102 and staggered	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:35
S10 4	1	("20040095532").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 12:36
S10 5	1	("20040095528").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 17:10
S10 6	2	((("20030231149") or ("20050092997")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 17:10
S10 7	1	("20040218109").PN.	US-PGPUB; USPAT	OR	OFF	2006/05/15 03:19
S10 8	0	(heterogeneous near straight) AND ((crystal\$5 adj2 boundary) with straight) AND ((semiconductive adj channel) (channel)) AND ((thin adj film adj transistor) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/15 03:21

EAST Search History

S10 9	3	((heterogeneous near straight) ((crystal\$5 adj2 boundary) with straight)) AND ((semiconductive adj channel) (channel)) AND ((thin adj film adj transistor) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/15 03:25
S11 0	1135	((heterogeneous near straight) (crystal\$5 adj2 boundary)) AND ((semiconductive adj channel) (channel)) AND ((thin adj film adj transistor) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/15 03:26
S11 1	290	S110 and (349/42-43.ccls. 257/59, 66,72,74.ccls. 345/92.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/15 03:25
S11 2	34	((heterogeneous near straight) (crystal\$5 adj2 boundary)) AND ((semiconductive adj channel) (channel)) AND ((thin adj film adj transistor) TFT)).CLM.	US-PGPUB	OR	ON	2006/05/15 03:26
S11 3	1	("20040263722").PN.	US-PGPUB; USPAT	OR	OFF	2006/05/15 09:28
S11 4	1	("20040218109").PN.	US-PGPUB; USPAT	OR	OFF	2006/08/31 12:00
S11 5	101287	((thin adj film) TFT) and ((channel) (semiconductor adj (film layer)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:15
S11 6	8738	S115 and ("349"/\$.ccls. 257/59,72. ccls. 345/92.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:12
S11 7	2017	S116 and (laser same (anneal\$5 irradiat\$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:14

EAST Search History

S11 8	81	S117 and (crystal\$5 adj boundary)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:20
S11 9	140	((thin adj film) TFT) AND ((channel) (semiconductor adj (film layer))) AND (laser same (anneal\$5 irradiat\$5)) AND (crystal\$5 adj boundary)	US-PGPUB	OR	ON	2006/08/31 12:19
S12 0	0	((thin adj film) TFT) AND ((channel) (semiconductor adj (film layer))) AND (laser same (anneal\$5 irradiat\$5)) AND (crystal\$5 adj boundary)).CLM.	US-PGPUB	OR	ON	2006/08/31 12:16
S12 1	37	((heterogeneous (crystal\$5 adj2 boundary)) AND ((semiconduct\$5 adj channel) (channel)) AND ((thin adj film adj transistor) TFT)).CLM.	US-PGPUB	OR	ON	2006/08/31 12:18
S12 2	287	((thin adj film) TFT) AND ((channel) (semiconductor adj (film layer))) AND (laser same (anneal\$5 irradiat\$5)) AND (crystal\$5 adj boundary)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:19
S12 3	222	S122 and @ad<"20040112"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 12:21
S12 4	1	("20040218109").PN.	US-PGPUB; USPAT	OR	OFF	2006/12/30 21:53
S12 5	1	("20040218109").PN.	US-PGPUB; USPAT	OR	OFF	2006/12/30 22:06